

**STRUCTURE AND METHOD OF FORMING BITLINE  
CONTACTS FOR A VERTICAL DRAM ARRAY USING A  
LINE BITLINE CONTACT MASK**

**ABSTRACT OF THE DISCLOSURE**

5           A bitline contact and method of forming bitline contact for a vertical DRAM array using a bitline contact mask. In the method, gate conductor lines are formed. An oxide layer is deposited over the gate conductor lines, and a bitline contact mask is formed over portions of the oxide layer. The  
10          bitline contact mask is etched, and a silicon layer is deposited on the substrate. A bitline layer is deposited on the silicon layer. A masking and etching operation is performed on the bitline layer.  
15          A M0 metal is deposited over the silicon layer and on sides of non etched portions of the bitline (M0) layer to form left and right bitlines.